



PATENT
Docket No. 150.00650102

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Brian A. Vaartstra et al.) Group Art Unit: 2815
Serial No.: 09/603,132) Examiner: E. Lee
Filed: June 23, 2000)
For: **DEVICE STRUCTURES INCLUDING RUTHENIUM SILICIDE DIFFUSION
BARRIER LAYERS**

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AMENDMENT AND RESPONSE
UNDER 37 CFR §1.116

Assistant Commissioner for Patents
Box AF
Washington D.C. 20231

COPY

Dear Sir:

The Final Office Action mailed September 14, 2001 has been received and reviewed.
Please amend the above identified application as follows:

In the Claims

Please amend claims 27, 32 and 36, and add new claims 39-44. The amended and new claims are provided below in clean form. Per 37 C.F.R. §1.121, amended claims are shown in Appendix A with notations to indicate changes made. For convenience, all pending claims, including those added hereby, are provided in Appendix A.

SUB E1
D1

27. (Twice Amended) A semiconductor device structure, the structure comprising:
a substrate assembly including a surface; and
a chemical vapor deposited diffusion barrier layer over at least a portion of the surface,
wherein the diffusion barrier layer is formed of RuSi_x , where x is in the range of about 0.01 to about 10.